

Schottky barrier diode

RB520S-30 New

●Applications

Low current rectification and high speed switching

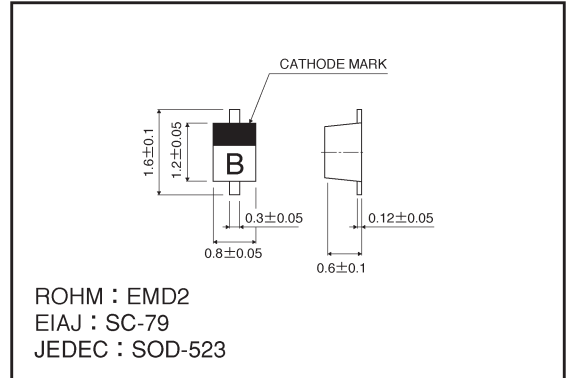
●Features

- 1) Small surface mounting type.(EMD2)
- 2) High reliability.
- 3) Low reverse current and low forward voltage.
(actual capability : $1\mu\text{A}$)

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge curren*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$

*60 Hz for 1 \sim

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.50	0.60	V	$I_F = 200\text{mA}$
Reverse current	I_R	—	0.1	1.0	μA	$V_R = 10\text{V}$

*ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

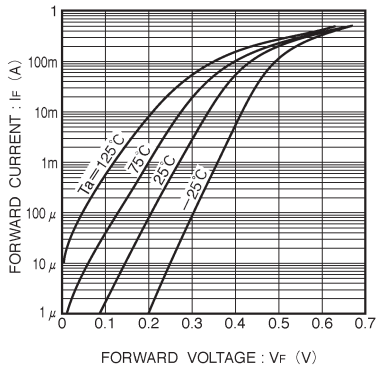


Fig. 1 Forward characteristics

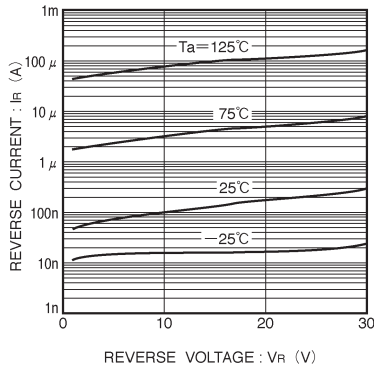


Fig. 2 Reverse characteristics

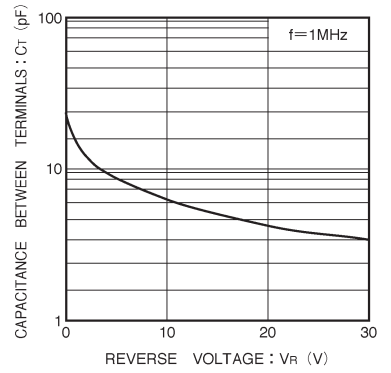


Fig. 3 Capacitance between terminals characteristics

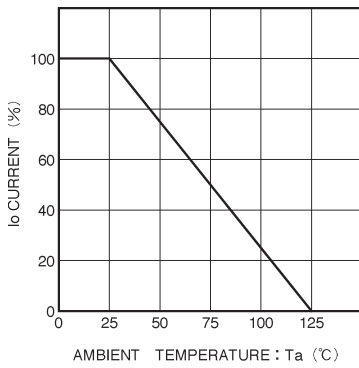


Fig. 4. Derating curve (mounting on glass epoxy PCBs)